



Curriculum Vitae : Marc M. Heyns

Marc Heyns was born in Turnhout, Belgium, on November 16, 1956.

He received the M.S. degree in Applied Sciences (Electronics) in 1979 from the Katholieke Universiteit Leuven, Belgium. In 1986 he received the Ph.D. degree, also from the Katholieke Universiteit Leuven, Belgium, with a thesis entitled: “Study of the charge trapping and degradation of thermally grown SiO₂ layers”.

From 1979 to 1985 he held a fellowship from the National Fund for Scientific Research (NFWO) in the Laboratory for Physics and Electronics of Semiconductors of the K.U. Leuven.

In January 1986 he joined IMEC where he became Department Director and Program Director responsible for a research group working on ultra-clean processing technology, advanced high- κ gate stacks, metal gates, epitaxial deposition of materials, environmentally benign processing and novel high-mobility substrate materials. Currently he is the program director of the “Explore” program performing exploratory research on nanotechnology, novel materials and devices for ultimate CMOS technology and novel memory concepts. He became an IMEC-Fellow in 2001 and a Professor at the Katholieke Universiteit Leuven at the Department of Metallurgy and Materials Engineering in 2005.

He has authored or co-authored more than 200 publications in scientific peer-reviewed journals, more than 600 contributions at scientific conferences, including more than 80 invited presentations, and has edited or contributed to various books. His current research topics include novel high- κ dielectric materials, advanced cleaning and surface preparation technology, epitaxy, novel devices made on high-mobility substrates such Ge and III/V compounds, tunnelFET's, nanowires, carbon nanotubes, graphene and new memory devices.

Short CV : Marc M. Heyns

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